

FIG. 1A

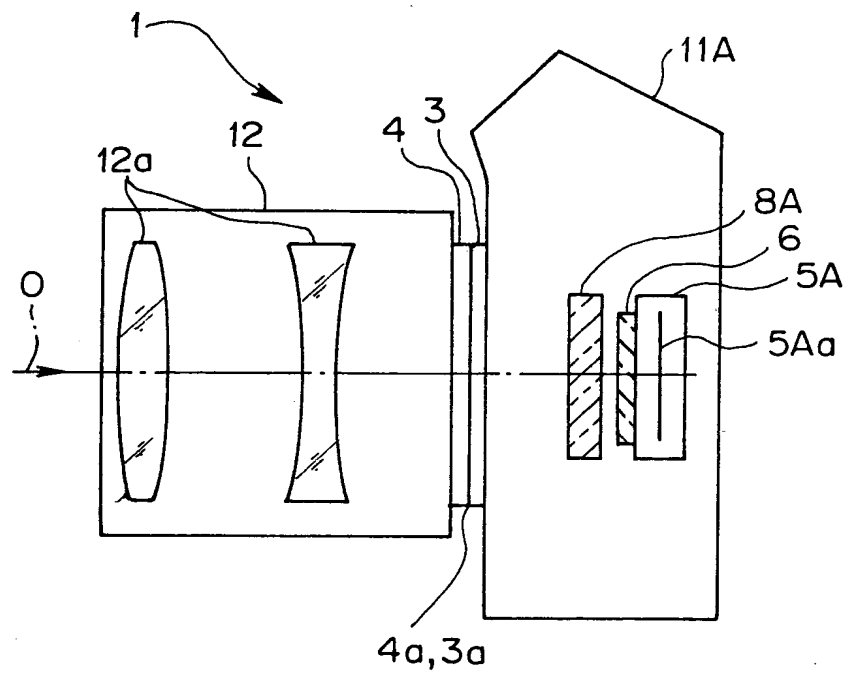


FIG. 1B

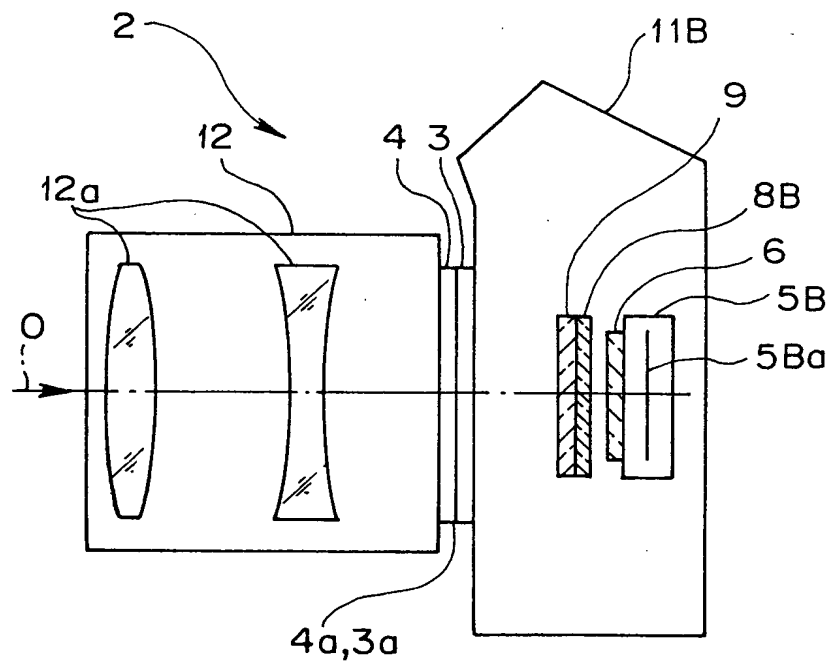


FIG. 2

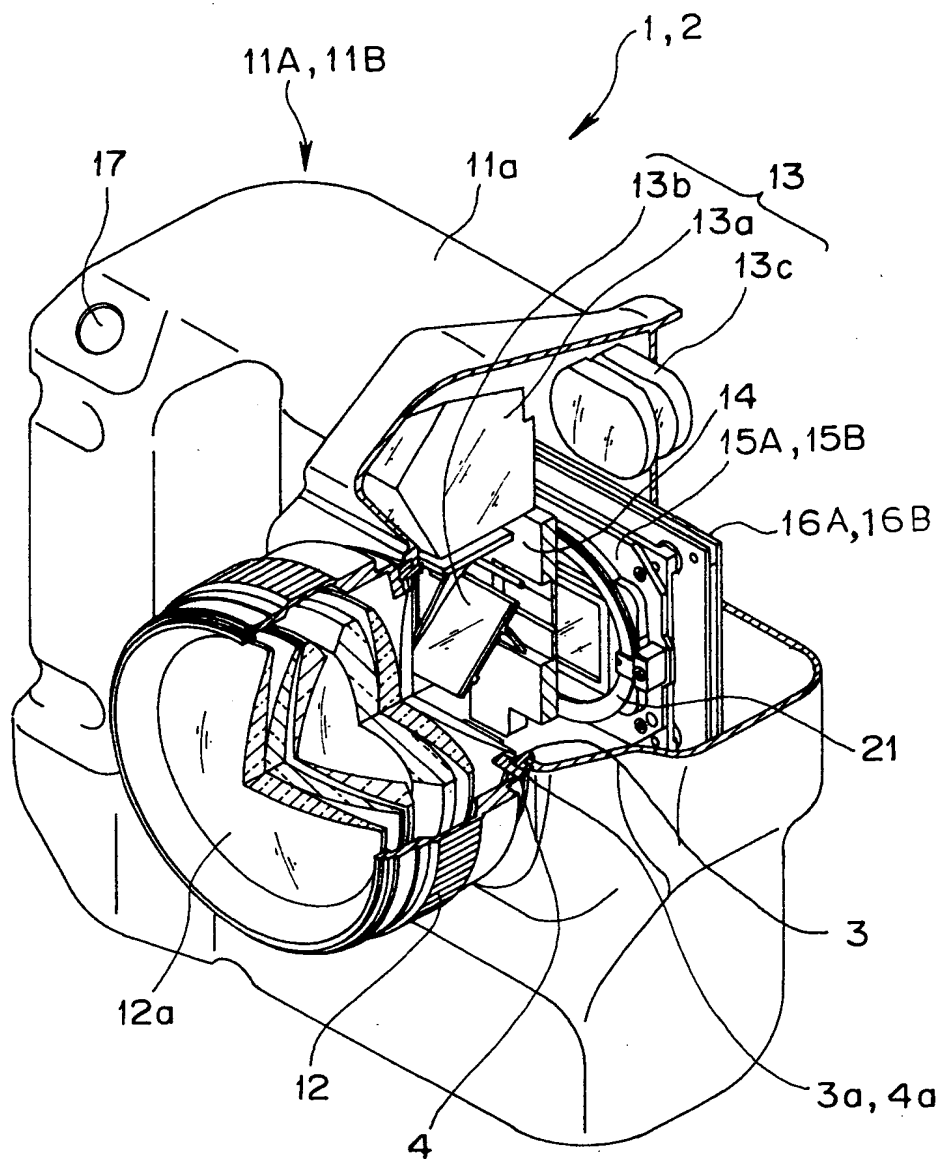


FIG. 3

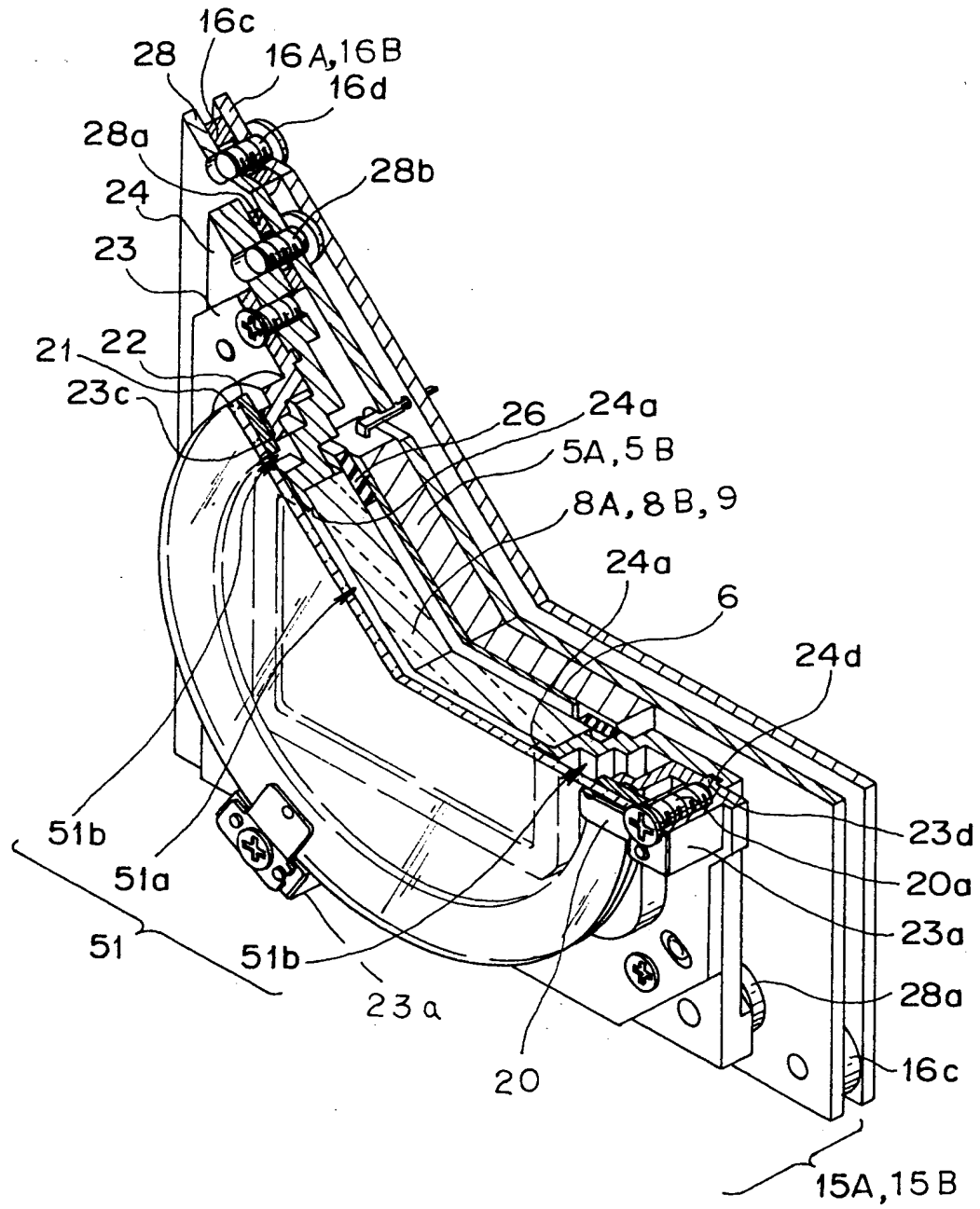
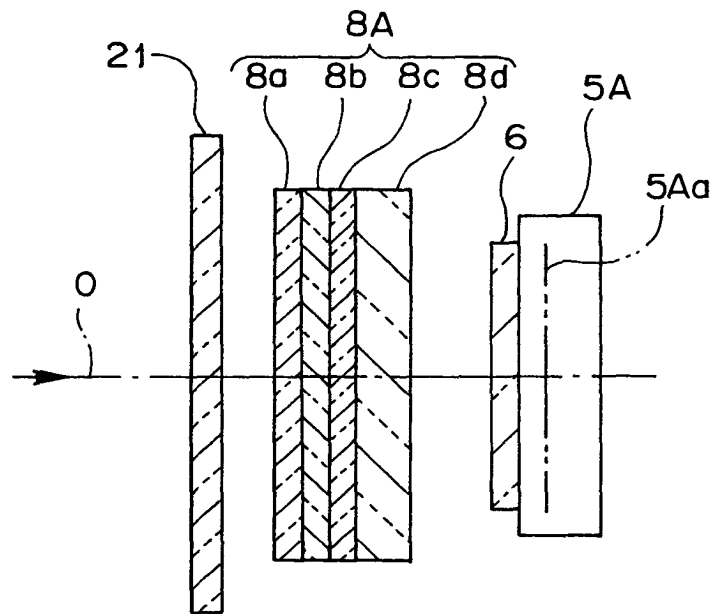


FIG. 4



A detailed cross-sectional diagram of a semiconductor device. The central core consists of alternating layers of p-type material (indicated by diagonal hatching) and n-type material (indicated by horizontal lines). From top to bottom, the layers are labeled 28, 28a, 28b, 28c, 28d, 28e, 29, 30, 31, 32, 33, 34, 35, 36, 37, 38, 39, 40, 41, 42, 43, 44, 45, 46, 47, 48, 49, 50, 51, 52, 53, 54, 55, 56, 57, 58, 59, 60, 61, 62, 63, 64, 65, 66, 67, 68, 69, 70, 71, 72, 73, 74, 75, 76, 77, 78, 79, 80, 81, 82, 83, 84, 85, 86, 87, 88, 89, 90, 91, 92, 93, 94, 95, 96, 97, 98, 99, 100. The top surface is labeled 11A. The bottom surface is labeled 15A. The side surfaces are labeled 16, 16c, 16d, 16e, 16f, 16g, 16h, 16i, 16j, 16k, 16l, 16m, 16n, 16o, 16p, 16q, 16r, 16s, 16t, 16u, 16v, 16w, 16x, 16y, 16z. The thickness of the substrate is indicated as t_{so}. Other labels include 21, 22, 23, 23a, 23b, 23c, 23d, 23e, 24, 24a, 24b, 24c, 24d, 24e, 24f, 24g, 24h, 24i, 24j, 24k, 24l, 24m, 24n, 24o, 24p, 24q, 24r, 24s, 24t, 24u, 24v, 24w, 24x, 24y, 24z, 25, 26, 27, 28, 28a, 28b, 28c, 28d, 28e, 29, 30, 31, 32, 33, 34, 35, 36, 37, 38, 39, 40, 41, 42, 43, 44, 45, 46, 47, 48, 49, 50, 51, 52, 53, 54, 55, 56, 57, 58, 59, 60, 61, 62, 63, 64, 65, 66, 67, 68, 69, 70, 71, 72, 73, 74, 75, 76, 77, 78, 79, 80, 81, 82, 83, 84, 85, 86, 87, 88, 89, 90, 91, 92, 93, 94, 95, 96, 97, 98, 99, 100.

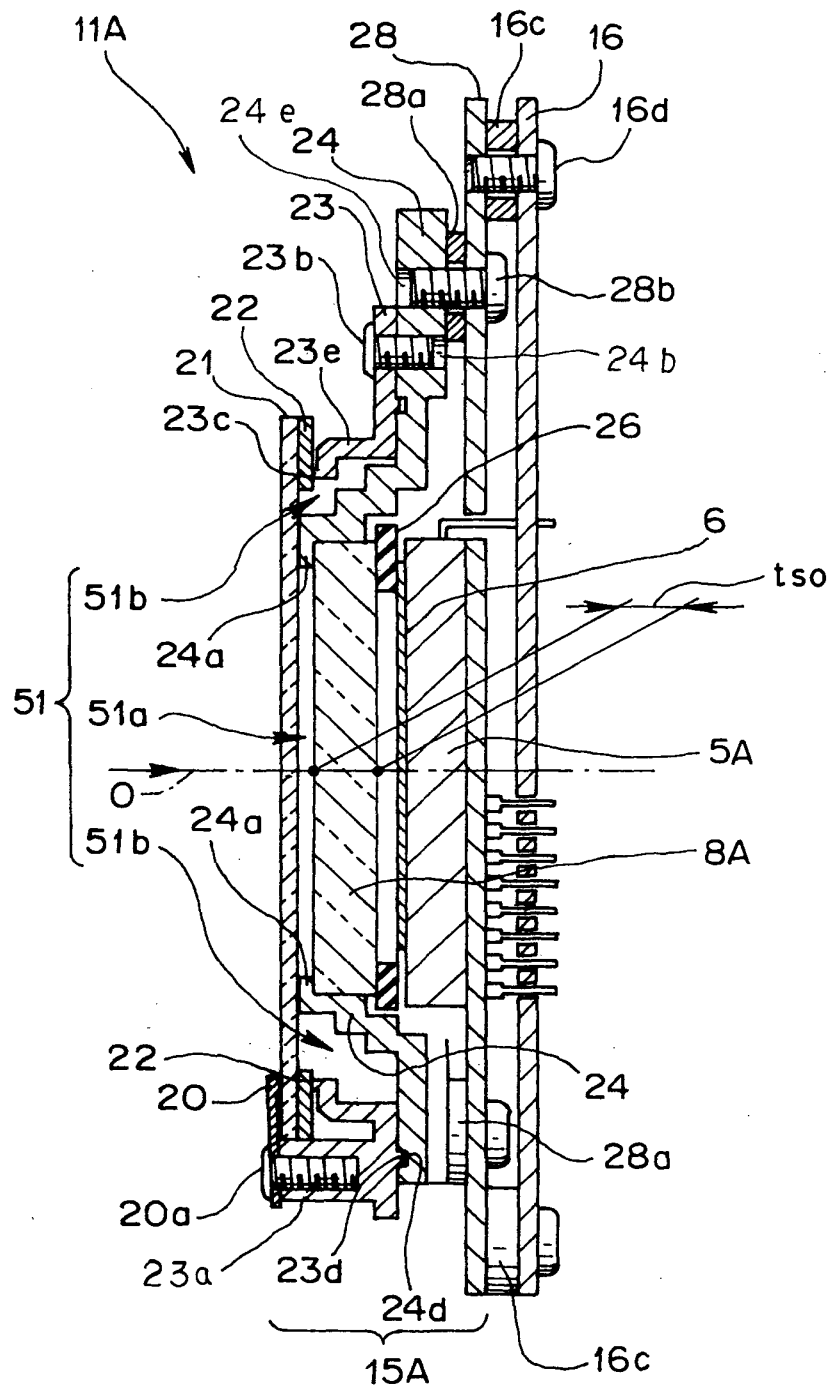


FIG. 7

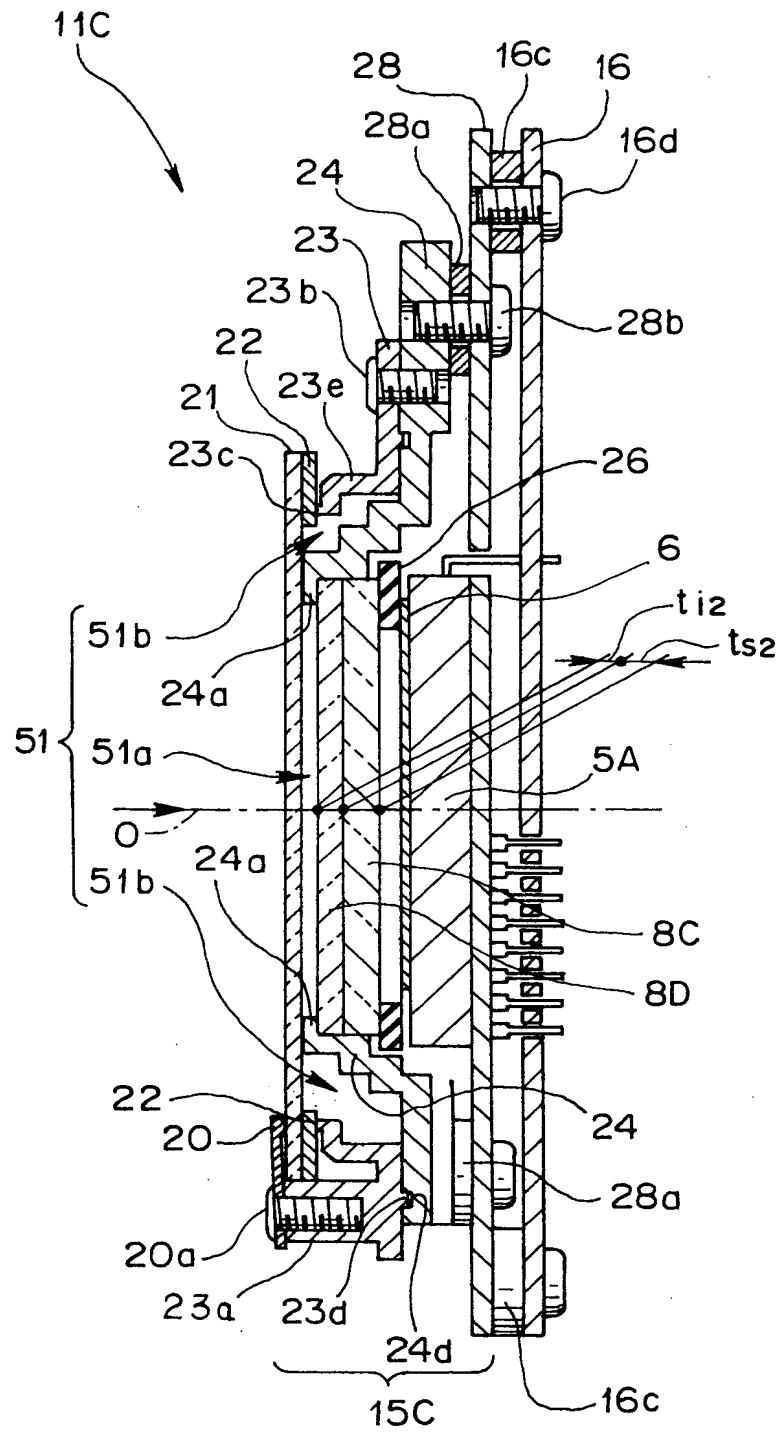


FIG. 8

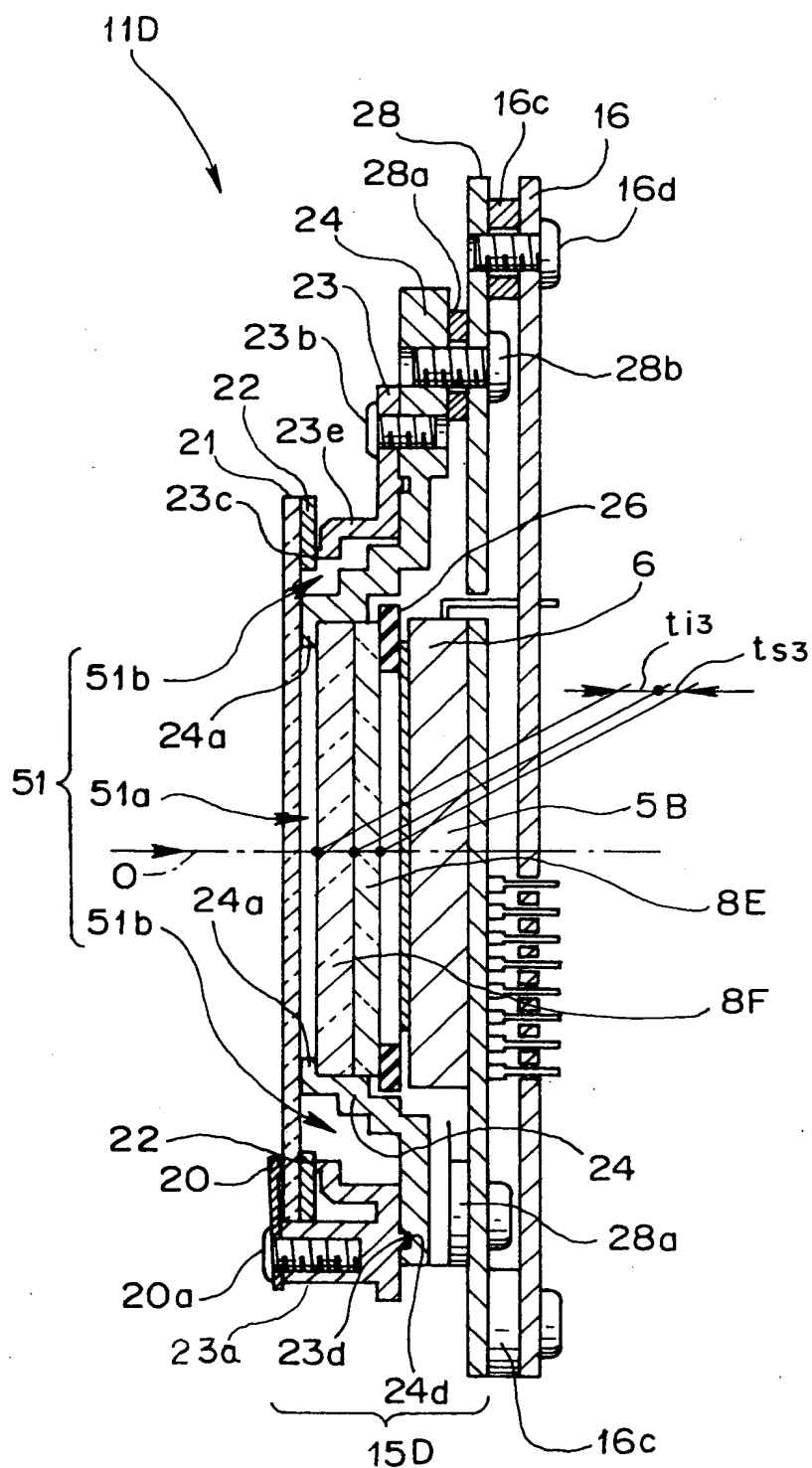


FIG. 9

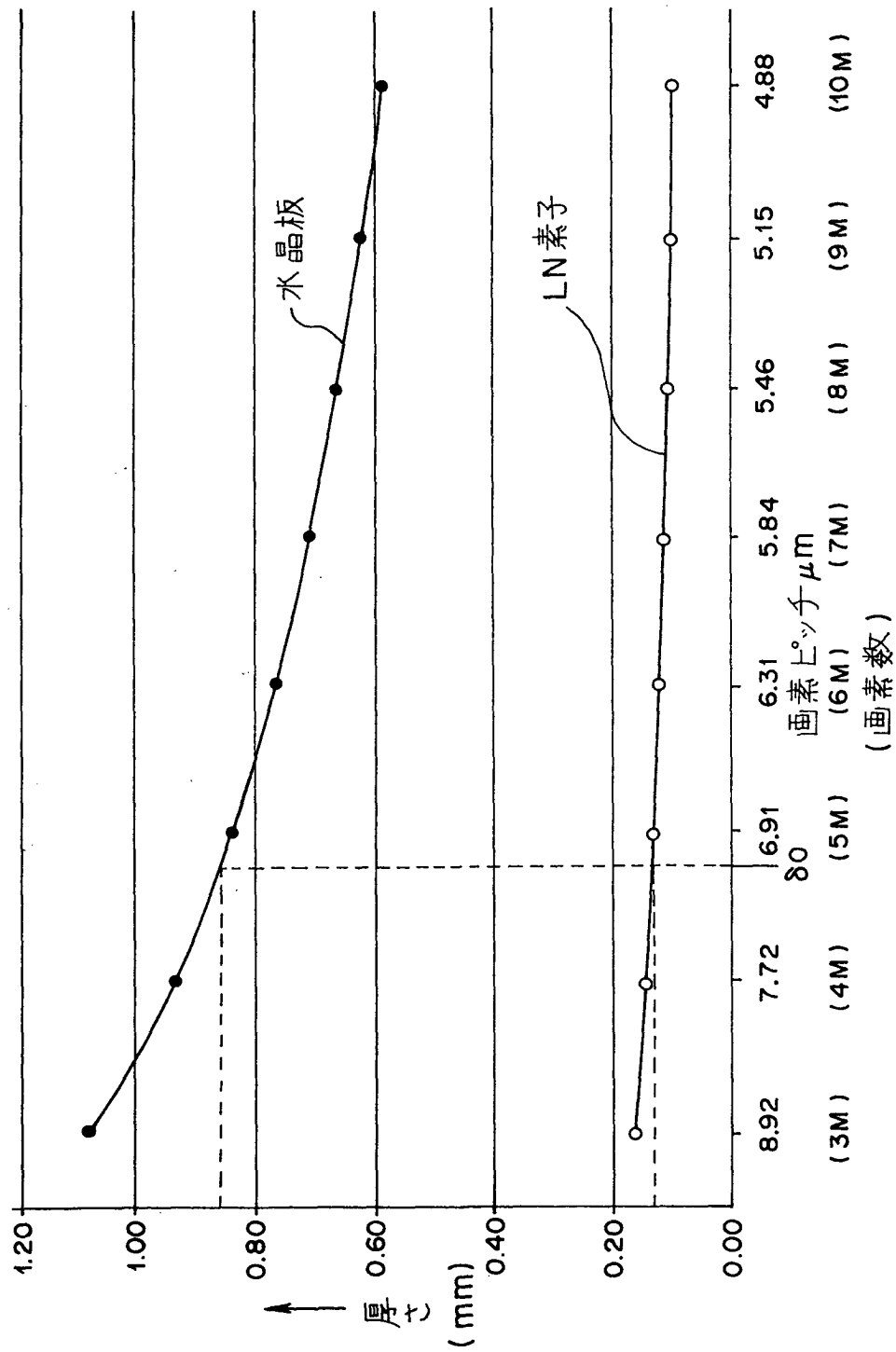


FIG. 10
RELATED ART

